

IN THE CLAIMS:

Please cancel Claims 6 and 12.

1-5 (Cancelled)

6. (Currently Cancelled)

7. (Currently amended) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm,

~~The substrate system of Claim 6, wherein the silicon is present in an amount ranging from 2 to 10 wt. %.~~

8. (Currently amended) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm,

~~The substrate system of Claim 6, wherein the refractory metal component is present in an amount ranging from 90 to 98 wt. %.~~

9. (Currently amended) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm,

~~The substrate system of Claim 6, wherein the substrate system has capacitance is that is at least 30,000 CV.~~

10. (Previously presented) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders, the refractory metal component being present in an amount ranging from 90 to 98 wt. % and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount ranging from 2 to 10 wt. %.

11. (Previously presented) The substrate system of Claim 10, wherein the

substrate system has capacitance is that is at least 30,000 CV.

12. (Cancelled)
13. (Currently amended) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm.
~~The substrate system of Claim 6, wherein the silicon is present in an amount ranging from 2 to 10 wt. %.~~
14. (Currently amended) A substrate system comprising a mixture of (i) a refractory metal component selected from the group consisting of tantalum powders, tantalum nitride powders, niobium powders, niobium nitride powders and (ii) a silicon component, wherein (a) the system has a capacitance that is at least 10,000 CV and (b) the silicon is present in an amount that is at least 500 ppm.
~~The substrate system of Claim 6, wherein the tantalum or the niobium is present in an amount ranging from 90 to 98 wt.%.~~